

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09296

DT-03-09

Silicon Epitaxial Planar Type

Diode

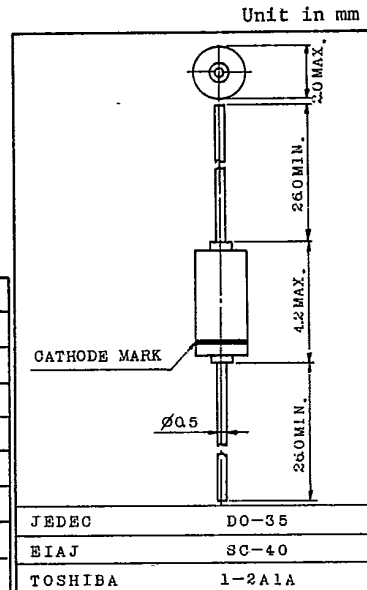
**1N4608**

TENTATIVE

COMMUNICATION AND INDUSTRIAL APPLICATIONS.  
HIGH VOLTAGE, ULTRA HIGH SPEED SWITCHING APPLICATIONS.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	VRM	85	V
Reverse Voltage	VR	70	V
Maximum (Peak) Forward Current	IFM	600	mA
Average Forward Current	IO	200	mA
Surge Current (1 μs)	IFSM	4	A
Power Dissipation	P	500	mW
Junction Temperature	Tj	200	°C
Storage Temperature Range	Tstg	-65 ~ 200	°C



Weight : 0.14g

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Breakdown Voltage	VBR	IR=100μA	85	-	-	V
Forward Voltage	VF(1)	IF=100μA	0.39	0.44	0.49	V
	VF(2)	IF=1mA	0.50	0.55	0.60	V
	VF(3)	IF=10mA	0.61	0.66	0.71	V
	VF(4)	IF=100mA	0.74	0.80	0.85	V
	VF(5)	IF=250mA	0.81	0.87	0.93	V
	VF(6)	IF=350mA	0.84	0.90	0.96	V
	VF(7)	IF=450mA	-	-	1.00	V
	VF(8)	IF=500mA	-	-	1.10	V
Reverse Current	IR(1)	VR=50V	-	-	100	nA
	IR(2)	VR=50V, Ta=100°C	-	-	25	μA
	IR(3)	VR=70V	-	-	250	nA
Total Capacitance	CT	VR=0, f=1MHz	-	-	4	pF
Reverse Recovery Time	t <sub>rr</sub> (1)	IF=IR=10mA, I <sub>rr</sub> =1mA	-	-	10	ns
	t <sub>rr</sub> (2)	IF=IR=500mA, I <sub>rr</sub> =50mA	-	-	15	ns

TOSHIBA CORPORATION